4 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

Features:

- Current transfer ratio
  (CTR:MIN.50% at IF =5mA ,VCE =5V)
  High isolation voltage between input and output
  (Viso=5000 V rms)
- Compact dual-in-line package
  FL817*:1-channel type
- Pb free

Options available:

- Leads with 0.4”(10.16mm) spacing (M Type)
- Leads bends for surface mounting (S Type)
- Tape and Reel of Type Ⅰ for SMD(Add”-TA” Suffix)
- Tape and Reel of TypeⅡ for SMD(Add”-TB” Suffix)
- The tape is 16mm and is wound on a 33cm reel

Applications:

- Computer terminals
- System appliances, measuring instruments
- Registers, copiers, automatic vending machines
- Cassette type recorder
- Electric home appliances, such as fan heaters, etc.
- Signal transmission between circuits of different potentials and impedances

Device Selection Guide

Part. No.	Chip Material	
	IR	PT
FL817*	GaAs	Silicon

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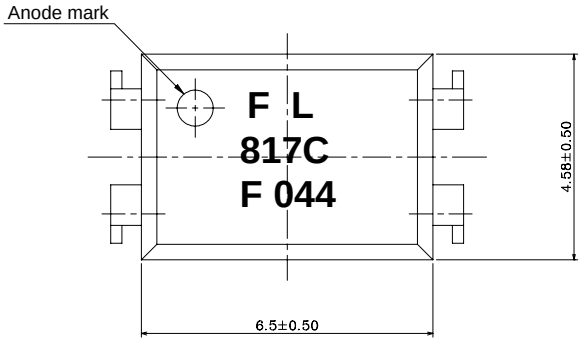
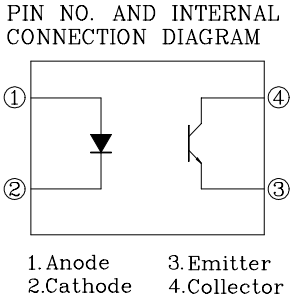
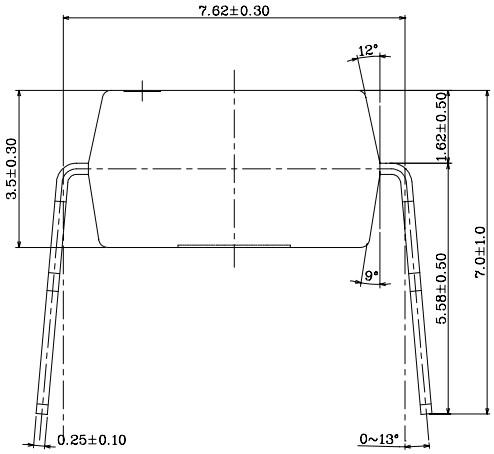
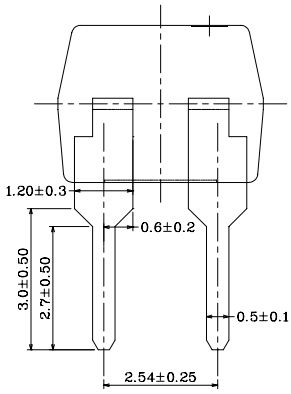
Package Dimensions



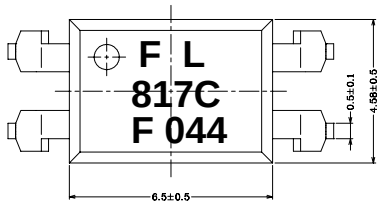


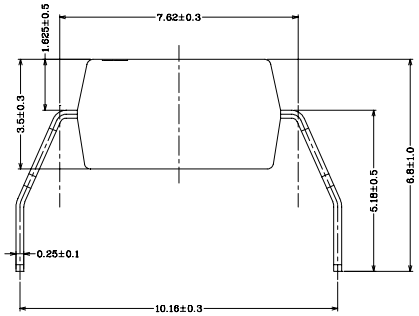


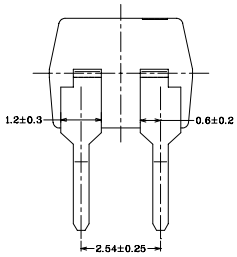


Package Dimensions

Type







Notes:

1. Rank shall be or shall not be marked
2. Year date code
3. 2-digit work week
4. All dimensions are in millimeters
5. Specifications are subject to change without notice

4 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I_F	50	mA
	Reverse Voltage	V_R	6	V
	Power Dissipation	P	70	mW
Output	Collector Power Dissipation	P_C	150	mW
	Collector Current	I_C	50	mA
	Collector-Emitter Voltage	V_{CEO}	70	V
	Emitter-Collector Voltage	V_{ECO}	6	V
Total Power Dissipation		Ptot	200	mW
*1 Isolation Voltage		Viso	5000	V rms
Operating Temperature		Topr	-55~+110	°C
Storage Temperature		Tstg	-55~+125	°C
*2 Soldering Temperature		Tsol	260	°C

*1 AC for 1 minute, R.H= 40~ 60%RH

-Isolation voltage shall be measured using the following method.

(1) Short between anode and cathode on the primary side and between collector, emitter and base on the secondary side.

(2) The isolation voltage tester with zero-cross circuit shall be used.

(3) The waveform of applied voltage shall be a sine wave

*2 For 10 seconds

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Electro-Optical Characteristics

(Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Condition
Input	Forward	V_F	-	1.2	1.4	V	I_F=20mA
	Reverse Current	I_R	-	-	10	uA	V_R=4V
	Terminal	Ct	-	30	250	pF	V=0,f=1kHz
Output	*Collector Dark current*	I_{CEO}	-	-	100	nA	V_{CE}=20V
	Collector-Emitter breakdown voltage	BV_{CEO}	70	100	-	V	Ic=0.1mA
Transfer Characteristics	Current Transfer ratio	CTR	50	-	600	%	I_F=5mA ,V_{CE}=5V
	Collector-Emitter saturation voltage	$V_{CE(sat)}$	-	0.1	0.2	V	I_F=20mA ,Ic=1 mA
	Isolation resistance	R_{ISO}	5×10^{10}	10^{11}	-	Ω	DC500V,40~60%R.H
	Floation capacitance	Cf	-	0.6	1.0	pF	V=0, f=1MHz
	Cut-off frequency	fc	-	80	-	kHz	V_{CE}=5V, I_C=2 mA R_L=100Ω, -3dB
	Rise time	t_r	-	4	18	us	V_{CE}=2V I_C=2mA,R_L=100Ω
	Fall time	t_f	-	3	18	us	

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Supplement

Current Transfer Ratio CTR

Sub-Model No.	Rank mark	CTR (%)	*Condition*
FL817 (A)	A	80 to 160	I_F = 5 mA V_{CE} = 5 V T_a = 25°C
FL817 (B)	B	130 to 260	
FL817 (C)	C	200 to 400	
FL817 (D)	D	300 to 600	

Fig. 1 Forward Current vs. Ambient Temperature

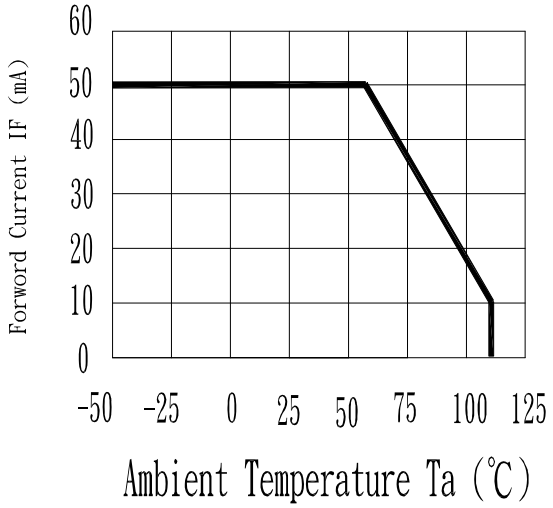

Fig.2 Collecter Power Dissipation vs. Ambient Temperature

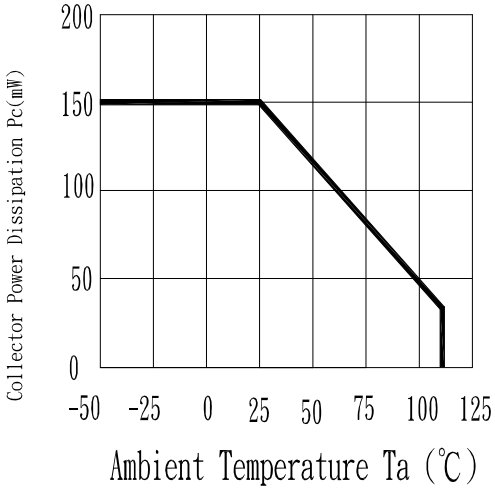

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Fig. 3 Collector−emitter Saturation Voltage vs. Forward Current (Ta=25°C)

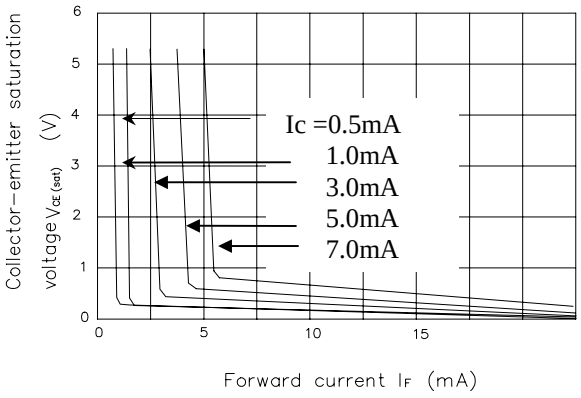

Fig.4 Current transfer Ratio vs. Forward Current

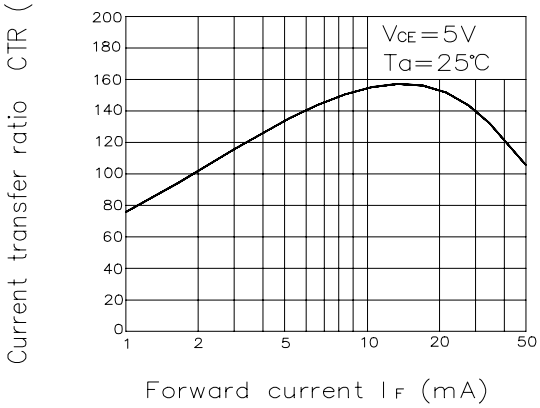

Fig.5 Forward Current vs. Forward Voltage Voltage

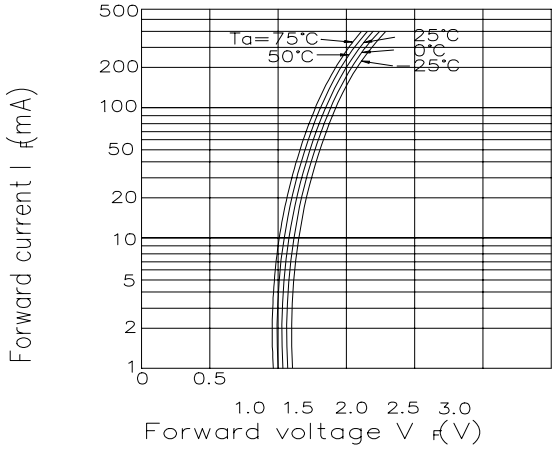

Fig.6 Collector Current vs. Collector−emitter Voltage (Ta=25°C)

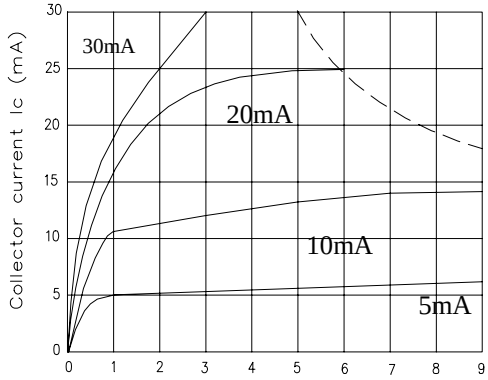

Fig.7 Relative Current Transfeer Ratio vs. Ambient Temperature

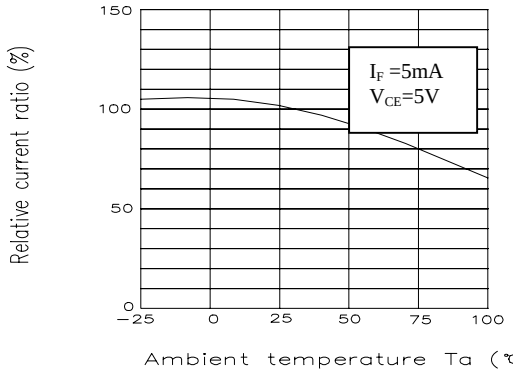

Fig.8 Collector−emitter Saturation Voltage vs. Ambient Temperature

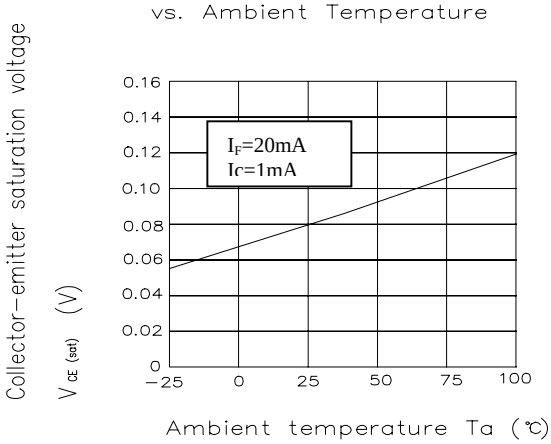

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Fig.9

Collector Dark Current vs. Ambient Temperature

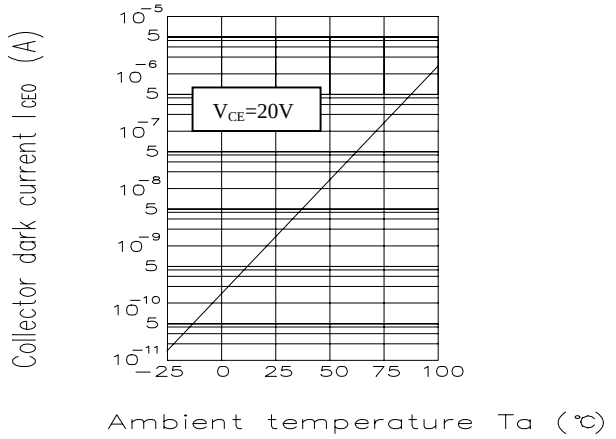


Fig.10

Response Time vs. Load Resistance

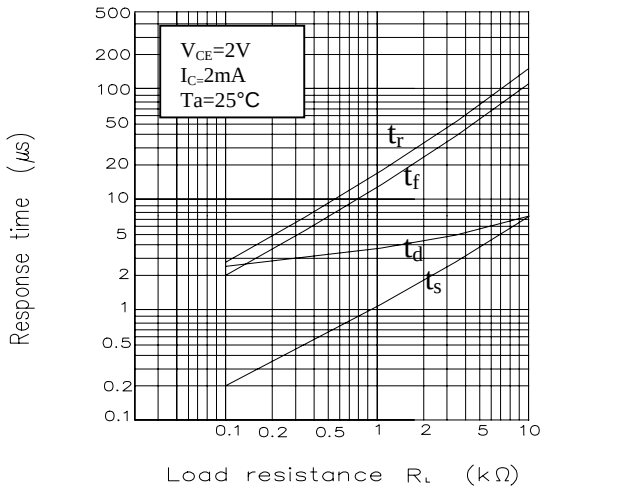
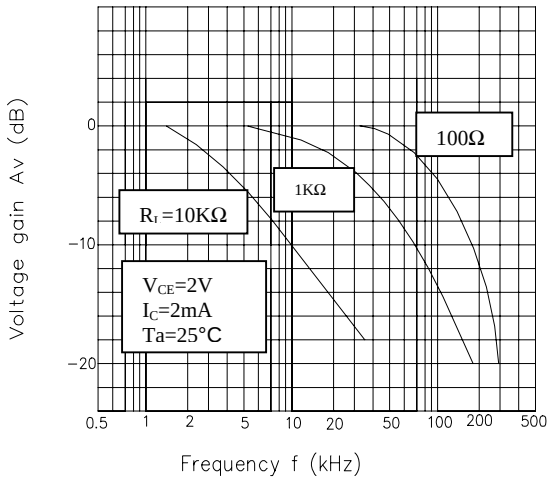
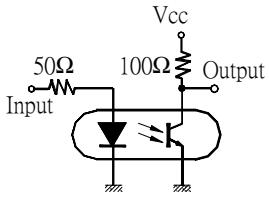
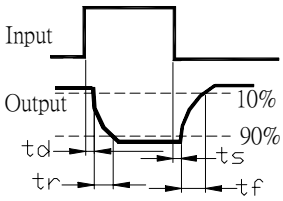


Fig.11

Frequency Response







4 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

RELIABILITY PLAN

- **The reliability of products shall be satisfied with items listed below.**

Confidence level : 90 % , LTPD : 10 %

Classification	Test Item	Description & Condition	(Acc.) Sample	Failure Criteria	Reference Standard
Endurance Test	**Operation Life ***	**Ta = 25 ± 3°C IR: If = 50 mA Pt: Pc = 130 mW (Vf=1.4v) , 1000 hrs**	**0 / 22**	**CTR shift > 1.2 Vf > U* 1.0 Ir > U * 1.0 Vce(sat) >U*1.0 Bvceo < L*1.0 Bveco < L*1.0 L :Low Spec.Limit U : Up Spec. Limit**	**MIL-S-750 : 1026 MIL-S-883 : 1005 JIS C 7021 : B-1**
	High Temperature / High Humidity Reverse Bias (H3TRB)	**Ta = 85 ± 3°C , Humi. = 85 % rh Pt: 80% * Vce (max rating) , 1000 hrs**	**0 / 22**		**JIS C 7021 : B-11**
	High Temperature Reverse Bias (HTRB)	**Ta = 105 ± 3°C Pt: 100% * Vce (Max rating) , 1000 hrs**	**0 / 22**		**JIS C 7021 : B-8**
	Low Temperature Storage	**Ta = -50 ± 3°C , 1000 hrs**	**0 / 22**		**JIS C 7021 : B-12**
	High Temperature Storage	**Ta = 125 ± 3°C , 1000 hrs**	**0 / 22**		**JIS C 7021 : B-10 MIL-S-883 : 1008**
	Auto clave	**P = 15 PSIG , Ta = 121 °C , Humi. = 100 % rh , 48 hrs**	**0 / 22**		**JESD 22-A102-B**
Environmental Test	**Temperature Cycling (Air to Air)**	**125°C ~ - 55 °C 30 ~ 30 min , 100 cycles**	**0 / 22**		**MIL-S-883 :1010 JIS C 7021 : A-4**
	Thermal Shock (Liquid to Liquid)	**125 ~ - 55°C t (dwell) = 5 min t (trans.) = 10 sec , 100 cycles**	**0 / 22**		**MIL-S-202 : 107D MIL-S-750 : 1051 MIL-S-883 :1011**
	Solder Resistance	**Ta = 260 ± 3°C t (dwell) = 10 ± 1 sec**	**0 / 22**		**MIL-S-750 : 2031 JIS C 7021 : A-1**
	Solder Ability	**Ta = 230 ± 3 °C t (dwell) = 5 ± 1 sec**	**0 / 22**		**MIL-S-883 : 2003 JIS C 7021 : A-2**

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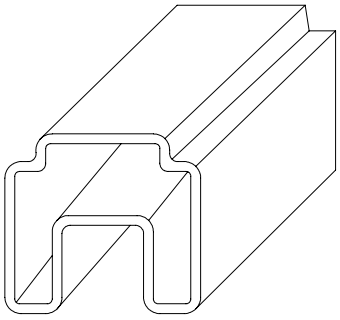
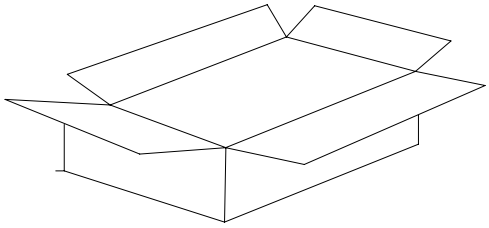
● Tube Packing Specifications (For Dip & Type)

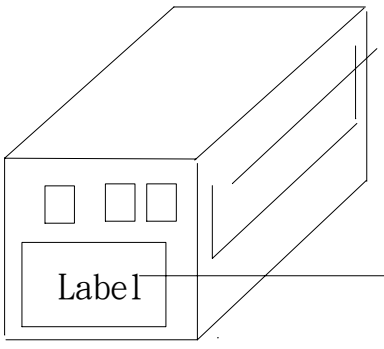
1. Tube



2. Inner Carton



3. Outside Carton



方晶科技股份有限公司
FANGJING TECHNOLOGY CO.,LTD

FL817 x

QTY:xxxx

RoHS

● Packing Quantity

1. 100 Pcs / Tube
2. 25 Tubes / Inner Carton
3. 12 Inner Cartons / Outside Carton